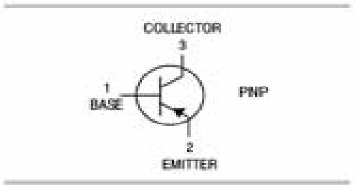
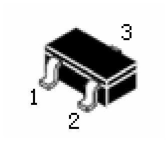
PNP Silicon Epitaxial Planar Transistor **2SA1579**

FEATURES

- Power dissipation.(P_C=200mW)
- Excellent H_{FE} Linearity.

Lead-free





SOT-323

APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1579	RP/ RR/RS	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-50	mA
P_C	Collector Dissipation	200	mW
$T_{j,}T_{stg}$	Junction and Storage Temperature	-55 to +150	℃

PNP Silicon Epitaxial Planar Transistor **2SA1579**

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

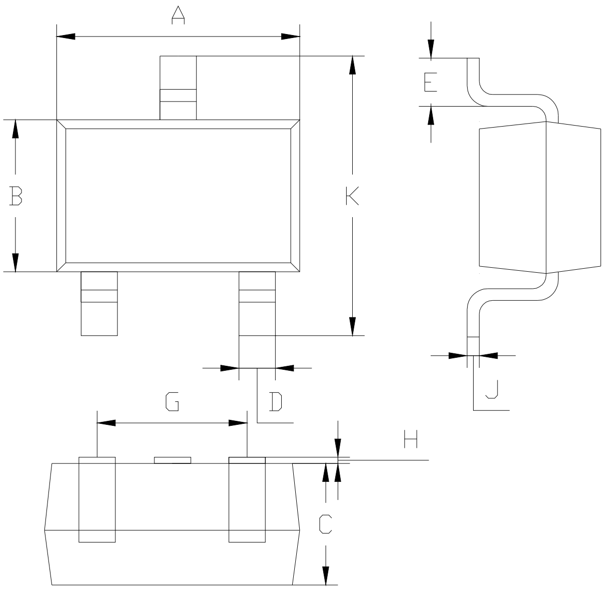
Parameter	**Symbol**	**Test conditions**	**MIN**	**TYP**	**MAX**	**UNIT**
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-50μA,I_E=0	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-50μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-100V,I_E=0			-0.5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.5	μA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-2mA	180		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA, I_B=-1mA			-0.5	V
Transition frequency	f_T	V_{CE}=-12V, I_C= -2mA f=30MHz		140		MHz
Collector output capacitance	C_{ob}	V_{CB}=-12V,I_E=0,f=1MHz		3.2		pF

CLASSIFICANTION OF h_{FE}

Rank	**P**	**R**	**S**
Range	120-270	180-390	270-560
marking	RP	RR	RS

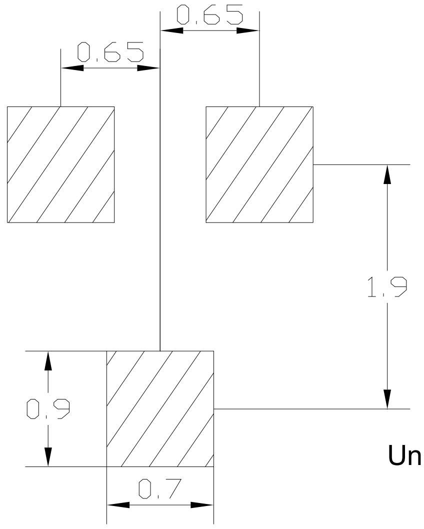
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	1.8	2.2
B	1.15	1.35
C	1.0Typical	
D	0.15	0.35
E	0.25	0.40
G	1.2	1.4
H	0.02	0.1
J	0.1Typical	
K	2.2	2.4
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SA1579	SOT-323	3000/Tape&Reel